

5.5V rated 2A capable slew rate controlled load switch

#### Features

- 1.8V to 5.5V operation voltage range
- Low quiescent current <1µA when disabled</li>
- Reverse current blocking when switch is off
- DIO7301B: Built-in 100Ω(typ) output discharge resistor
- 48mΩ(typ) N-MOSFET Resistor:
- DC Current Up to 2A (max.)
- Peak Current Up to 5A (max.)
- Built-in Soft-Start 3ms
- Active High with Integrated Bridge
- Pb-Free Device SOT23-5

#### Applications

- Cell Phone and Digital Camera
- PDA and Notebook
- LCD Monitor
- TV and Set-Top Box

#### **Block Diagram**

#### **Descriptions**

The DIO7301/1B is a Low On-Resistance N-channel MOSFET controlled by a soft-start sequence of 3ms for mobile applications.

The low  $R_{DS}(on)$  allows system supplying or battery charging up to DC 2A.The device is enable automatically if a power supply is connected on  $V_{IN}$  pin (active High) and maintained off if no power input (internal pull down).

Due to the current consumption optimization, the leakage current is drastically decreased from the battery connected to the device, which allows extending the battery life.



#### Typical Application





#### **Ordering Information Order Part** Тор **Output Discharge** $\mathbf{T}_{\mathbf{A}}$ Package Number Marking Resistance DIO7301ST5 YWXW NO -40 to +85°C Tape & Reel, 3000 Green SOT23-5 DIO7301BST5 YWXV Yes Green -40 to +85°C SOT23-5 Tape & Reel, 3000 **Marking Definition Product Serical No** Product code YWXW YWXV Internal code Internal batch number Week Code Week Code Year Code Year Code Pin 1 Identification Pin 1 Identification **Pin Assignments** 0 NC 5 OUT 1 GND 2 EN 3 4 IN **Pin Description**

# Pin Description

Pin	Name	Туре	Description
1	NC	NC	Not connect. Connect to GND Recommended.
2	GND	Power	GND
3	EN	Input	Enable input, logic high active.
4	IN	Power	Switch Input voltage; connect a $1\mu$ F or greater ceramic capacitor from IN to GND as close as possible to the IC.
5	OUT	Output	Switch Output; connect a $1\mu F$ capacitor from OUT to GND as close as possible to the IC.



### **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Rating" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maxim rating conditions for extended periods may affect device reliability.

	Parameter	Rating	Unit	
V <sub>IN</sub>		-0.3 to 6	V	
V <sub>OUT</sub> ,EN		-0.3 to 6	V	
Storage Temperature		-65 to 150	°C	
Maximum Junction Ra	nge	-40 to 145	°C	
Thermal Resistance, 6	ALG	190	°C/W	
Power Dissipation, (T <sub>A</sub> =25°C)		526	mW	
Latch Up Protection		200	mA	
ESD	HBM, JEDEC: JESD22-A114	6		
	CDM, JEDEC : JESD22-C101	2		

### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation to ensure optimal performance to the datasheet specifications. DIOO does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>IN</sub>	Operational Power Supply		1.8		5.5	V
V <sub>EN</sub>	Enable Voltage		0		5.5	V
C <sub>IN</sub>	Decoupling input capacitor		1			μF
C <sub>OUT</sub>	Decoupling output capacitor	USB port per Hub	1			μF
Ι <sub>Ουτ</sub>	Maximum DC Current	T <sub>A</sub> =25°C			2	А
I <sub>PEAK</sub>	Maximum Peak Current	1ms pulse width at 217Hz ,T <sub>A</sub> =25°C			5	А
T <sub>A</sub>	Ambient Temperature Range		-40	25	85	°C
TJ	Junction Temperature Range		-40	25	125	°C



### **Electrical Characteristics**

 $T_{\text{A}}\text{=}25^{\circ}\text{C}$  V  $_{\text{IN}}$  = 5V, unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Tun	Max.	Unit	
Symbol			Conditions		Тур.	IVIAX.	Unit	
POWER SV	WITCH							
R <sub>DS(ON)</sub>	Static drain-source on-state resistance	V <sub>IN</sub> =5V,T <sub>A</sub> = 25°C	; 	40	48	60	mΩ	
		I <sub>OUT</sub> =200mA,-40°C< T <sub>A</sub> <85°C				85	mΩ	
t <sub>R</sub>	Switch turn-on edge rising time	V <sub>IN</sub> =4.5V	$C_{LOAD}$ =100µF,R <sub>LOAD</sub> =150Ω	2	2.5	5	ms	
t <sub>F</sub>	Switch turn-off edge falling time	V <sub>IN</sub> =4.5V	C <sub>LOAD</sub> =100μF,R <sub>LOAD</sub> =150Ω (DIO7301)	17	35	52	ms	
			C <sub>LOAD</sub> =100μF,R <sub>LOAD</sub> =150Ω (DIO7301B)	9	13	17	ms	
t <sub>DON</sub>	Switch turn-on delay	V <sub>IN</sub> =4.5V; C <sub>LOAD</sub> =100µF	50% of EN pin to $V_{\text{OUT}}\text{=}10\%$ of fully on	0.7	1.5	2.3	ms	
t <sub>DOFF</sub>	switch turn-off delay	V <sub>IN</sub> =4.5V; C <sub>LOAD</sub> =100µF	50% of EN pin to $V_{\text{OUT}}\text{=}90\%$ of fully on	7.5	15	22.5	μs	
ENABLE IN								
V <sub>IH</sub>	High-level input voltage			1.45			V	
V <sub>IL</sub>	Low-level input voltage					0.85	V	
R <sub>PD</sub>	Pull-down resistance at EN pin	$T_A = -45^{\circ}C \text{ to } +85^{\circ}C$			1		MΩ	
REVERSE	-LEAKAGE PROTECTION							
I <sub>REV</sub>	Reverse-current protection	V <sub>IN</sub> =0V, V <sub>OUT</sub> =4.2V, -40°C< T <sub>A</sub> <85°C, EN="0"			1	2	μΑ	
QUIESCEN	QUIESCENT CURRENT							
Ι <sub>Q</sub>	Current consumption	V <sub>IN</sub> =5V, V <sub>OUT</sub> floating, EN =5V			100	140	μA	
I <sub>SDN</sub>	shutdown current	V <sub>IN</sub> =5V, En="0", V <sub>OUT</sub> =GND,-40°C< T <sub>A</sub> <85°C				1	μA	
Note: This parameter is guaranteed by design and characterization								

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## **Application information**

#### Enable

Enable pin voltage in the active high means on. This part is automatically turned on when the input voltage enables the device. In the other side, this part is turned off when the input voltage is not available, which limits current consumption from battery to  $V_{OUT}$  pin.

#### Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush currents, an input capacitor is placed to the  $V_{IN}$  and GND as close as possible. The value of the input capacitor is recommended 1µF at least. Higher values capacitor can help to further reduce the voltage drop.

#### **Output Capacitor**

While the device works, a capacitor from 100nF to  $1\mu$ Facross V<sub>OUT</sub> and GND is recommended to accommodate load transient condition. It also helps to prevent parasitic inductance forces V<sub>OUT</sub> below GND when switching off. Output capacitor has the minimal effect on device's turn on slew rate time.

#### **Blocking Control**

The blocking control circuitry switches the bulk of the power NMOS. When the part is off (No  $V_{IN}$  or EN tied to GND externally), the body diode limits the leakage current  $I_{REV}$  from OUT to IN. In this condition, the anode of the body diode is connected to IN pin and the cathode is connected to OUT pin. During the operation, the anode of the body diode is connected to OUT pin and the cathode is connected to IN pin to prevent the discharge of the power supply.





 $T_A=25^{\circ}C V_{IN} = 5V$ , unless otherwise noted.



 $V_{IN}$ =5V,  $R_{OUT}$ =5 $\Omega$ ,  $C_{OUT}$ =100 $\mu$ F, Turn on delay time

 $V_{IN}$ =5V,  $R_{OUT}$ =5 $\Omega$ ,  $C_{OUT}$ =100 $\mu$ F, Turn off delay time



 $V_{IN}$ =5V,  $R_{OUT}$ =5.1 $\Omega$ ,  $V_{IN}$  Startup











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